

NX3L2267S

Low-ohmic dual single-pole double-throw analog switch

Rev. 1 — 23 August 2011

Product data sheet

1. General description

The NX3L2267S is a dual low-ohmic single-pole double-throw analog switch suitable for use as an analog or digital 2 : 1 multiplexer/demultiplexer. Each switch has a digital select input (nS), two independent inputs/outputs (nY0 and nY1) and a common input/output (nZ).

The NX3L2267S includes termination resistors that improve noise immunity during overshoot excursions, off-isolation coupling, or pop-minimization.

Schmitt trigger action at the digital inputs makes the circuit tolerant to slower input rise and fall times. Low threshold digital inputs allows this device to be driven by 1.8 V logic levels in 3.3 V applications without significant increase in supply current I_{CC} . This makes it possible for the NX3L2267S to switch 4.3 V signals with a 1.8 V digital controller, eliminating the need for logic level translation. The NX3L2267S allows signals with amplitude up to V_{CC} to be transmitted from nZ to nY0 or nY1, or from nY0 or nY1 to nZ. Its low ON resistance (0.5 Ω) and flatness (0.13 Ω) ensures minimal attenuation and distortion of transmitted signals.

2. Features and benefits

- Wide supply voltage range from 1.4 V to 4.3 V
- Very low ON resistance (peak):
 - ◆ 1.65 Ω (typical) at $V_{CC} = 1.4$ V
 - ◆ 0.95 Ω (typical) at $V_{CC} = 1.65$ V
 - ◆ 0.55 Ω (typical) at $V_{CC} = 2.3$ V
 - ◆ 0.50 Ω (typical) at $V_{CC} = 2.7$ V
 - 0.50 Ω (typical) at $V_{CC} = 4.3$ V
- Break-before-make switching
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114F Class 3A exceeds 7500 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD78B Class II Level A
- 1.8 V control logic at $V_{CC} = 3.6$ V
- Control input accepts voltages above supply voltage
- Very low supply current, even when input is below V_{CC}
- High current handling capability (350 mA continuous current under 3.3 V supply)



- Specified from -40 °C to +85 °C and from -40 °C to +125 °C

3. Applications

- Cell phone
- PDA
- Portable media player

4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
NX3L2267SGU	-40 °C to +125 °C	XQFN10	plastic, extremely thin quad flat package; no leads; 10 terminals; body 1.40 × 1.80 × 0.50 mm	SOT1160-1

5. Marking

Table 2. Marking

Type number	Marking code
NX3L2267SGU	MS

6. Functional diagram

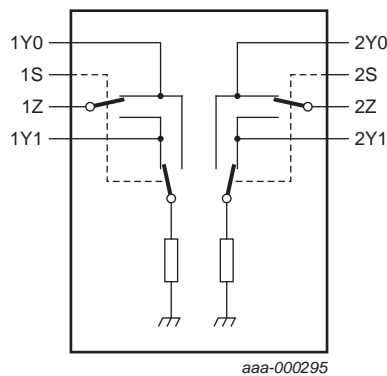


Fig 1. Logic symbol

7. Pinning information

7.1 Pinning

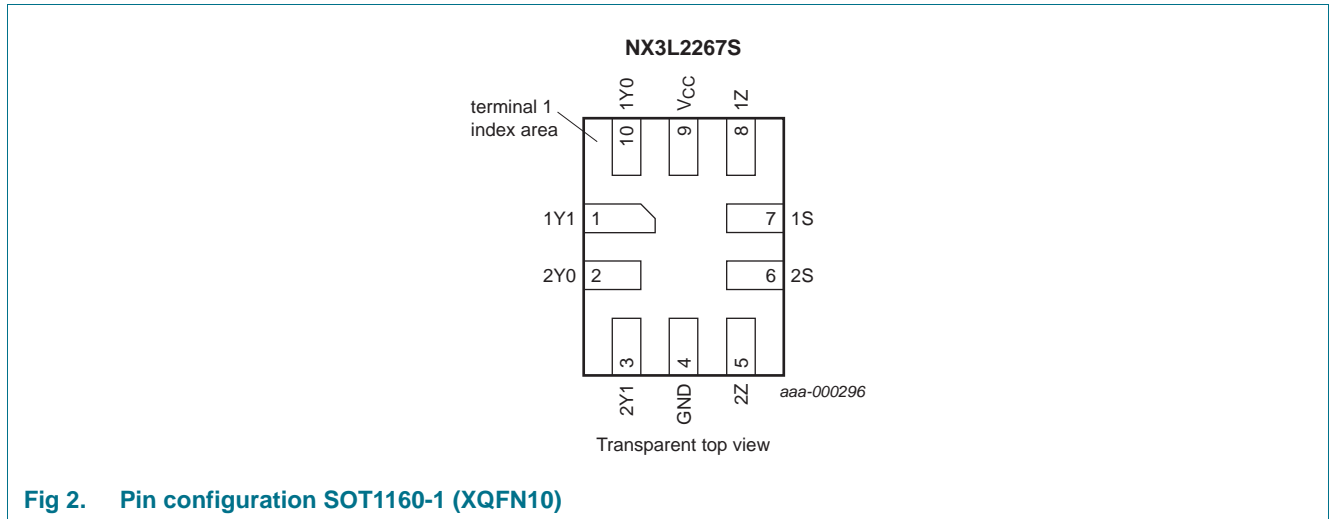


Fig 2. Pin configuration SOT1160-1 (XQFN10)

7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1Y0	10	independent input or output
1Y1	1	independent input or output
2Y0	2	independent input or output
2Y1	3	independent input or output
GND	4	ground (0 V)
2Z	5	common output or input
2S	6	select input
1S	7	select input
1Z	8	common output or input
V _{CC}	9	supply voltage

8. Functional description

Table 4. Function table^[1]

Input nS	Channel on
L	nY0 = nZ; nY1 terminated to GND
H	nY1 = nZ; nY0 terminated to GND

[1] H = HIGH voltage level; L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
V_I	input voltage	select input nS	^[1] -0.5	+4.6	V
V_{SW}	switch voltage	nZ ON or OFF; nYn ON	^[2] -0.5	$V_{CC} + 0.5$	V
		nYn OFF	0	1.4	V
I_{IK}	input clamping current	$V_I < -0.5$ V	-50	-	mA
I_{SK}	switch clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	± 50	mA
I_{SW}	switch current	$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V; source or sink current	-	± 350	mA
		$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	± 500	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[3] -	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed but may not exceed 4.6 V.

[3] For XQFN10 package: above 133 °C the value of P_{tot} derates linearly with 11.5 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		1.4	4.3	V
V_I	input voltage	select input nS	0	4.3	V
V_{SW}	switch voltage	switch input nY0 or nY1	^[1] 0	V_{CC}	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.4$ V to 4.3 V	^[2] -	200	ns/V

[1] To avoid sinking GND current from terminal nZ when switch current flows in terminal nYn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no GND current will flow from terminal nYn. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to select input nS signal levels.

11. Static characteristics

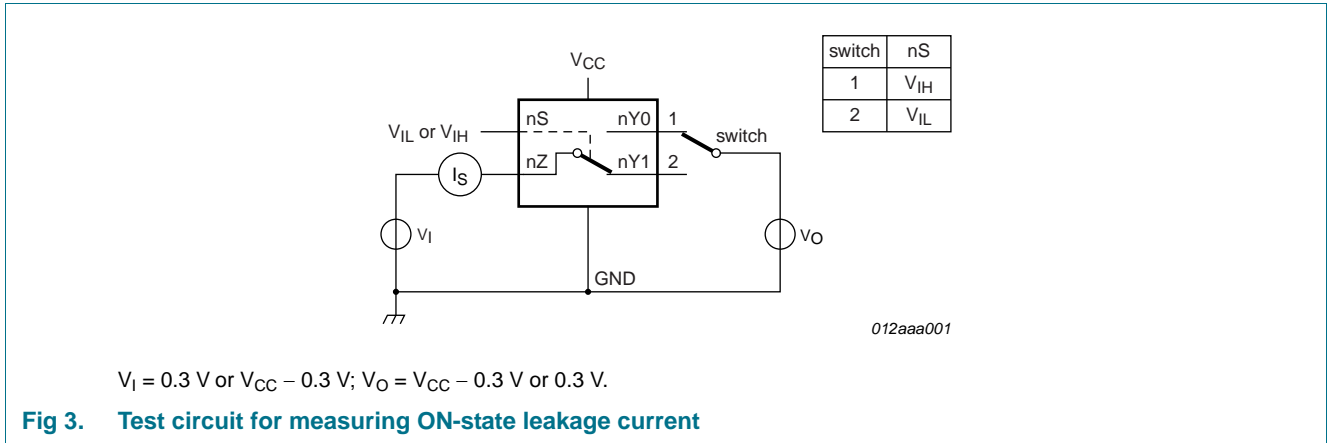
Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.4 V to 1.6 V	0.9	-	-	0.9	-	-	V
		V _{CC} = 1.65 V to 1.95 V	0.9	-	-	0.9	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.1	-	-	1.1	-	-	V
		V _{CC} = 2.7 V to 3.6 V	1.3	-	-	1.3	-	-	V
		V _{CC} = 3.6 V to 4.3 V	1.4	-	-	1.4	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.4 V to 1.6 V	-	-	0.3	-	0.3	0.3	V
		V _{CC} = 1.65 V to 1.95 V	-	-	0.4	-	0.4	0.3	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.5	-	0.5	0.4	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.5	-	0.5	0.5	V
		V _{CC} = 3.6 V to 4.3 V	-	-	0.6	-	0.6	0.6	V
I _I	input leakage current	select input nS; V _I = GND to 4.3 V; V _{CC} = 1.4 V to 4.3 V	-	-	-	-	±0.5	±1	µA
I _{S(ON)}	ON-state leakage current	nZ port; see Figure 3 V _{CC} = 1.4 V to 4.3 V	-	-	±50	-	±150	±1500	nA
I _{CC}	supply current	V _I = V _{CC} or GND; V _{SW} = GND or V _{CC}	-	-	-	-	-	-	-
		V _{CC} = 3.6 V	-	-	100	-	300	3000	nA
		V _{CC} = 4.3 V	-	-	150	-	500	5000	nA
ΔI _{CC}	additional supply current	V _{SW} = GND or V _{CC}	-	-	-	-	-	-	-
		V _I = 2.6 V; V _{CC} = 4.3 V	-	2.0	4.0	-	7	7	µA
		V _I = 2.6 V; V _{CC} = 3.6 V	-	0.35	0.7	-	1	1	µA
		V _I = 1.8 V; V _{CC} = 4.3 V	-	7.0	10.0	-	15	15	µA
		V _I = 1.8 V; V _{CC} = 3.6 V	-	2.5	4.0	-	5	5	µA
R _T	termination resistance	V _{SW} = 1.0 V; V _{CC} = 3.0 V [1]	-	200	-	-	-	-	Ω
			-	-	-	-	-	-	-
C _I	input capacitance		-	1.0	-	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance	port nYn	-	35	-	-	-	-	pF
C _{S(ON)}	ON-state capacitance	port nYn	-	135	-	-	-	-	pF

[1] Guaranteed by characterization, not production tested.

11.1 Test circuits



11.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see Figure 5 to Figure 11.

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit	
			Min	Typ ^[1]	Max	Min	Max		
R _{ON(peak)}	ON resistance (peak)	port nYn; V _I = GND to V _{CC} ; I _{SW} = 100 mA; see Figure 4	V _{CC} = 1.4 V	-	1.65	3.7	-	4.1	Ω
			V _{CC} = 1.65 V	-	0.95	1.6	-	1.7	Ω
			V _{CC} = 2.3 V	-	0.55	0.8	-	0.9	Ω
			V _{CC} = 2.7 V	-	0.50	0.75	-	0.9	Ω
			V _{CC} = 4.3 V	-	0.50	0.75	-	0.9	Ω
			ΔR _{ON}	ON resistance mismatch between channels	V _I = GND to V _{CC} ; I _{SW} = 100 mA		[2]		
		V _{CC} = 1.4 V	-	0.20	0.35	-	0.35	Ω	
		V _{CC} = 1.65 V	-	0.20	0.25	-	0.30	Ω	
		V _{CC} = 2.3 V	-	0.09	0.13	-	0.15	Ω	
		V _{CC} = 2.7 V	-	0.09	0.125	-	0.15	Ω	
		V _{CC} = 4.3 V	-	0.09	0.125	-	0.15	Ω	

Table 8. ON resistance ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see [Figure 5](#) to [Figure 11](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
$R_{ON(Flat)}$	ON resistance (flatness)	port nYn; $V_I = GND$ to V_{CC} ; $I_{SW} = 100$ mA						
		$V_{CC} = 1.4$ V	-	1.05	3.35	-	3.65	Ω
		$V_{CC} = 1.65$ V	-	0.55	1.25	-	1.35	Ω
		$V_{CC} = 2.3$ V	-	0.20	0.35	-	0.40	Ω
		$V_{CC} = 2.7$ V	-	0.18	0.35	-	0.40	Ω
		$V_{CC} = 4.3$ V	-	0.23	0.40	-	0.45	Ω

- [1] Typical values are measured at $T_{amb} = 25$ °C.
- [2] Measured at identical V_{CC} , temperature and input voltage.
- [3] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

11.3 ON resistance test circuit and graphs

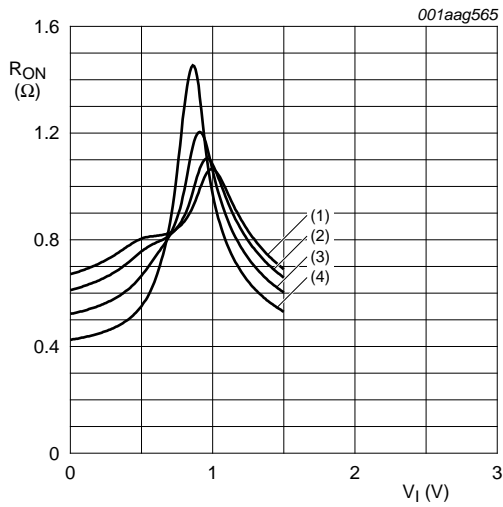
$R_{ON} = V_{SW} / I_{SW}$.

- (1) $V_{CC} = 1.5$ V.
- (2) $V_{CC} = 1.8$ V.
- (3) $V_{CC} = 2.5$ V.
- (4) $V_{CC} = 2.7$ V.
- (5) $V_{CC} = 3.3$ V.
- (6) $V_{CC} = 4.3$ V.

Measured at $T_{amb} = 25$ °C.

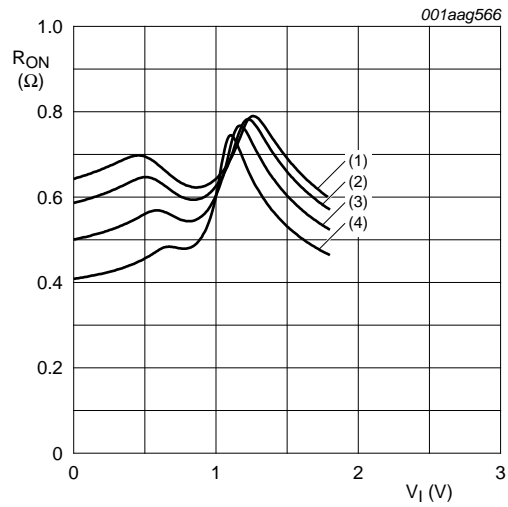
Fig 4. Test circuit for measuring ON resistance

Fig 5. Typical ON resistance as a function of input voltage (nYn port)



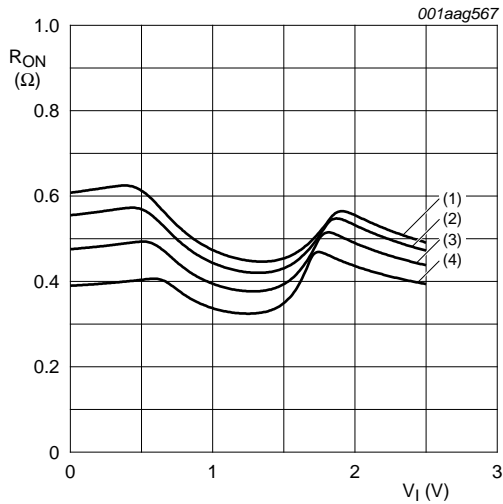
- (1) $T_{amb} = 125\text{ °C.}$
- (2) $T_{amb} = 85\text{ °C.}$
- (3) $T_{amb} = 25\text{ °C.}$
- (4) $T_{amb} = -40\text{ °C.}$

Fig 6. ON resistance as a function of input voltage; $V_{CC} = 1.5\text{ V}$ (nYn port)



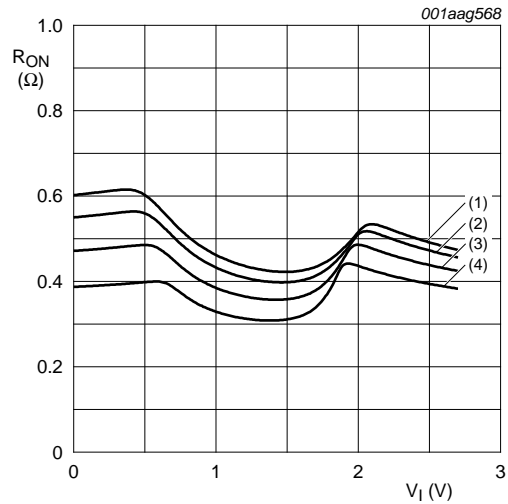
- (1) $T_{amb} = 125\text{ °C.}$
- (2) $T_{amb} = 85\text{ °C.}$
- (3) $T_{amb} = 25\text{ °C.}$
- (4) $T_{amb} = -40\text{ °C.}$

Fig 7. ON resistance as a function of input voltage; $V_{CC} = 1.8\text{ V}$ (nYn port)



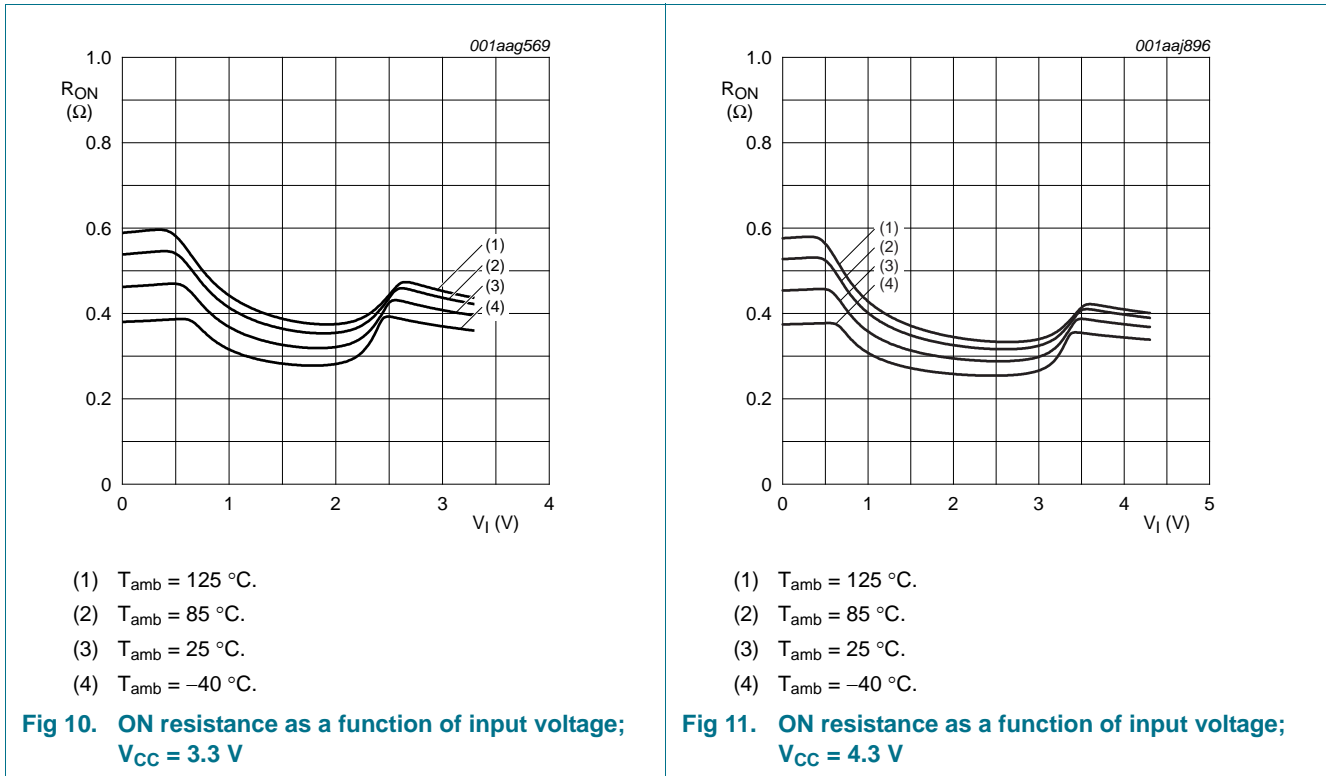
- (1) $T_{amb} = 125\text{ °C.}$
- (2) $T_{amb} = 85\text{ °C.}$
- (3) $T_{amb} = 25\text{ °C.}$
- (4) $T_{amb} = -40\text{ °C.}$

Fig 8. ON resistance as a function of input voltage; $V_{CC} = 2.5\text{ V}$ (nYn port)



- (1) $T_{amb} = 125\text{ °C.}$
- (2) $T_{amb} = 85\text{ °C.}$
- (3) $T_{amb} = 25\text{ °C.}$
- (4) $T_{amb} = -40\text{ °C.}$

Fig 9. ON resistance as a function of input voltage; $V_{CC} = 2.7\text{ V}$ (nYn port)



12. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 14](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{en}	enable time	nS to nZ or nYn; see Figure 12							
		V _{CC} = 1.4 V to 1.6 V	-	50	90	-	120	120	ns
		V _{CC} = 1.65 V to 1.95 V	-	36	70	-	80	90	ns
		V _{CC} = 2.3 V to 2.7 V	-	24	45	-	50	55	ns
		V _{CC} = 2.7 V to 3.6 V	-	22	40	-	45	50	ns
		V _{CC} = 3.6 V to 4.3 V	-	22	40	-	45	50	ns
t _{dis}	disable time	nS to nZ or nYn; see Figure 12							
		V _{CC} = 1.4 V to 1.6 V	-	32	70	-	80	90	ns
		V _{CC} = 1.65 V to 1.95 V	-	20	55	-	60	65	ns
		V _{CC} = 2.3 V to 2.7 V	-	12	25	-	30	35	ns
		V _{CC} = 2.7 V to 3.6 V	-	10	20	-	25	30	ns
		V _{CC} = 3.6 V to 4.3 V	-	10	20	-	25	30	ns

Table 9. Dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 14](#).

Symbol	Parameter	Conditions	T _{amb} = 25 °C			T _{amb} = -40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{b-m}	break-before-make time	see Figure 13 ^[2]							
		V _{CC} = 1.4 V to 1.6 V	-	19	-	9	-	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	17	-	7	-	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	13	-	4	-	-	ns
		V _{CC} = 2.7 V to 3.6 V	-	10	-	3	-	-	ns
		V _{CC} = 3.6 V to 4.3 V	-	10	-	2	-	-	ns

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.5 V, 1.8 V, 2.5 V, 3.3 V and 4.3 V respectively.

[2] Break-before-make guaranteed by design.

12.1 Waveform and test circuits

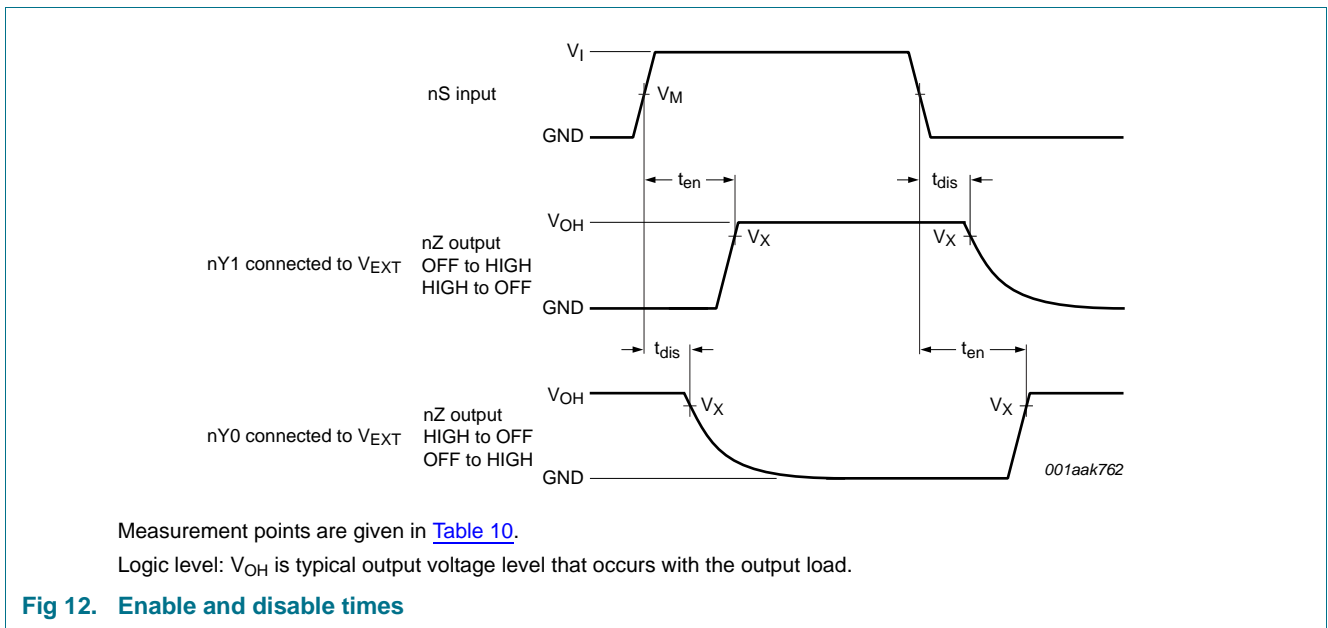


Table 10. Measurement points

Supply voltage	Input	Output
V _{CC}	V _M	V _X
1.4 V to 4.3 V	0.5V _{CC}	0.9V _{OH}

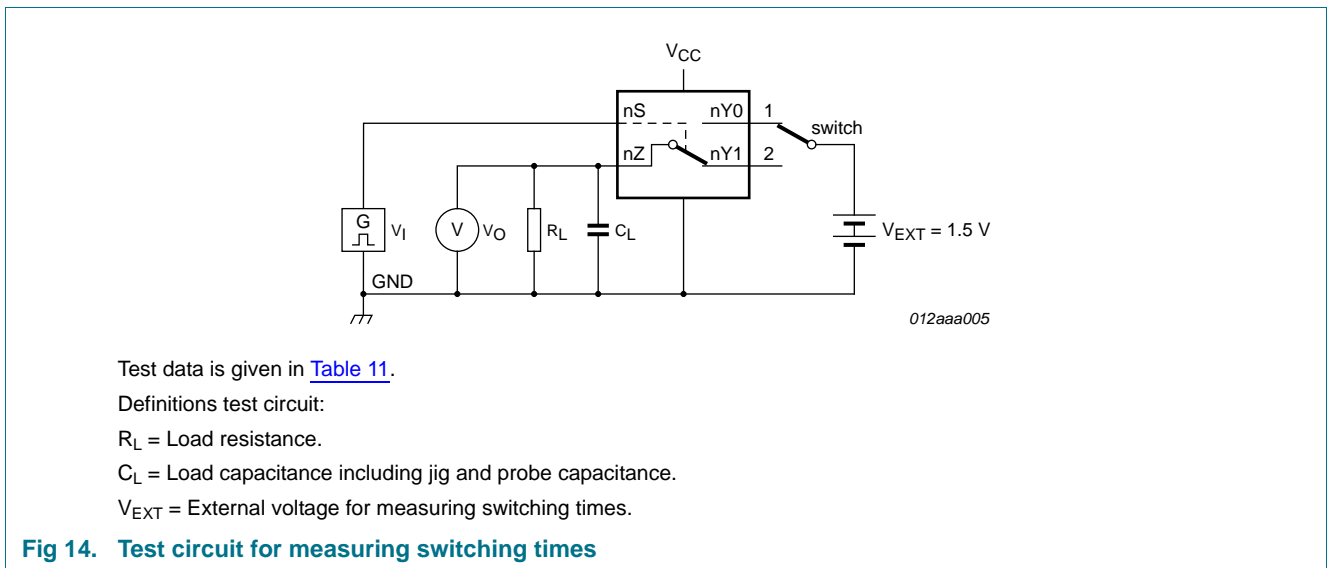
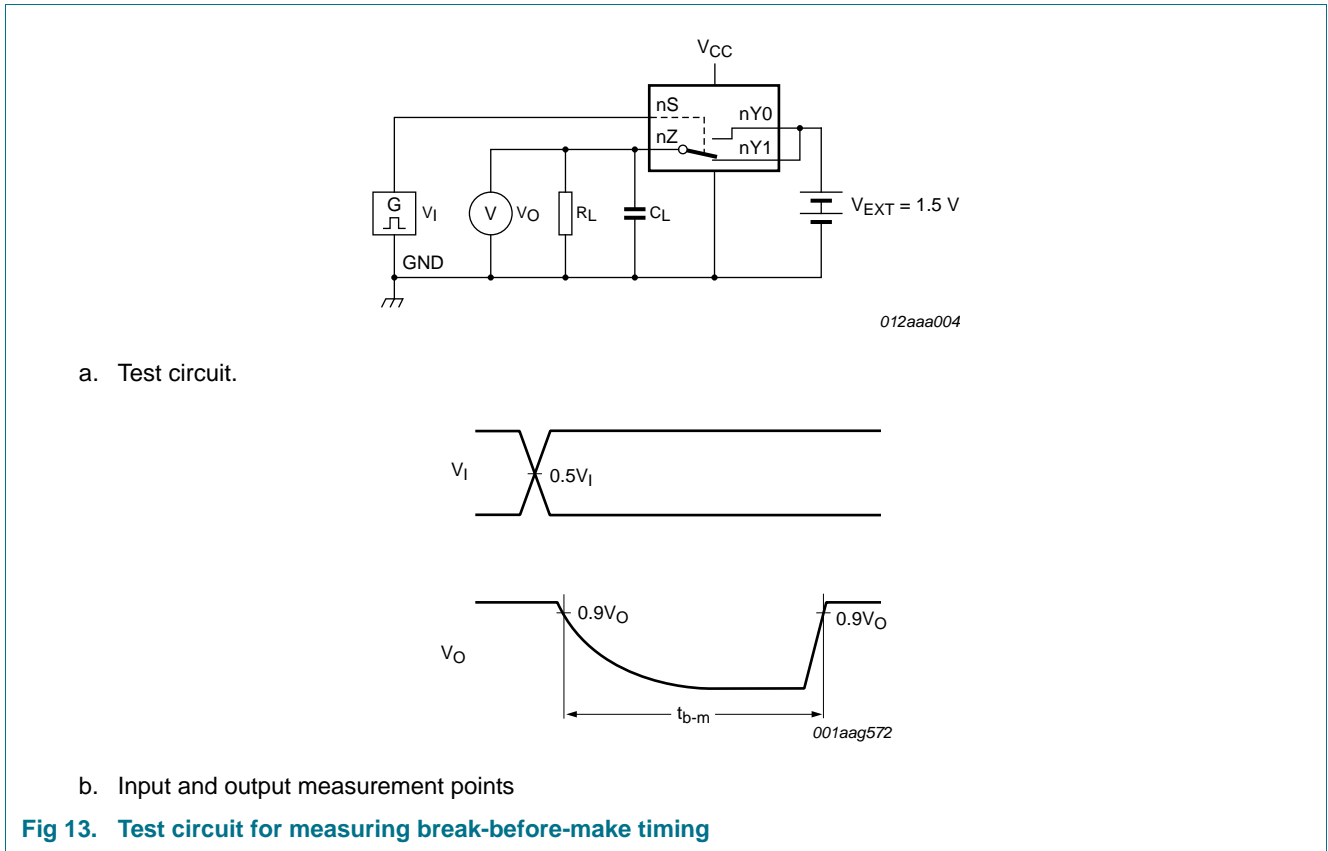


Table 11. Test data

Supply voltage	Input		Load	
V_{CC}	V_I	t_r, t_f	C_L	R_L
1.4 V to 4.3 V	V_{CC}	≤ 2.5 ns	35 pF	50 Ω

12.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = \text{GND}$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5 \text{ ns}$.

Symbol	Parameter	Conditions	T _{amb} = 25 °C			Unit
			Min	Typ	Max	
THD	total harmonic distortion	$f_i = 20 \text{ Hz to } 20 \text{ kHz}; R_L = 32 \text{ } \Omega$; see Figure 15 [1]				
		$V_{CC} = 1.4 \text{ V}; V_I = 1 \text{ V (p-p)}$	-	0.15	-	%
		$V_{CC} = 1.65 \text{ V}; V_I = 1.2 \text{ V (p-p)}$	-	0.10	-	%
		$V_{CC} = 2.3 \text{ V}; V_I = 1.5 \text{ V (p-p)}$	-	0.02	-	%
		$V_{CC} = 2.7 \text{ V}; V_I = 2 \text{ V (p-p)}$	-	0.02	-	%
		$V_{CC} = 4.3 \text{ V}; V_I = 2 \text{ V (p-p)}$	-	0.02	-	%
		$V_{CC} = 3.0 \text{ V}; V_I = 1 \text{ V (p-p)}; R_L = 600 \text{ } \Omega$	-	0.01	-	%
$f_{(-3\text{dB})}$	-3 dB frequency response	$R_L = 50 \text{ } \Omega$; see Figure 16 [1]				
		port nYn; $V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	60	-	MHz
α_{iso}	isolation (OFF-state)	$f_i = 100 \text{ kHz}; R_L = 50 \text{ } \Omega$; see Figure 17 [1]				
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	-90	-	dB
V_{ct}	crosstalk voltage	between digital inputs and switch; $f_i = 1 \text{ MHz}; C_L = 50 \text{ pF}; R_L = 50 \text{ } \Omega$; see Figure 18				
		$V_{CC} = 1.4 \text{ V to } 3.6 \text{ V}$	-	0.21	-	V
		$V_{CC} = 3.6 \text{ V to } 4.3 \text{ V}$	-	0.30	-	V
Xtalk	crosstalk	between switches; [1] $f_i = 100 \text{ kHz}; R_L = 50 \text{ } \Omega$; see Figure 19				
		$V_{CC} = 1.4 \text{ V to } 4.3 \text{ V}$	-	-90	-	dB
Q_{inj}	charge injection	$f_i = 1 \text{ MHz}; C_L = 0.1 \text{ nF}; R_L = 1 \text{ M}\Omega; V_{\text{gen}} = 0 \text{ V}; R_{\text{gen}} = 0 \text{ } \Omega$; see Figure 20				
		$V_{CC} = 1.5 \text{ V}$	-	4	-	pC
		$V_{CC} = 1.8 \text{ V}$	-	6	-	pC
		$V_{CC} = 2.5 \text{ V}$	-	16	-	pC
		$V_{CC} = 3.3 \text{ V}$	-	24	-	pC
		$V_{CC} = 4.3 \text{ V}$	-	37	-	pC

[1] f_i is biased at $0.5V_{CC}$.

12.3 Test circuits

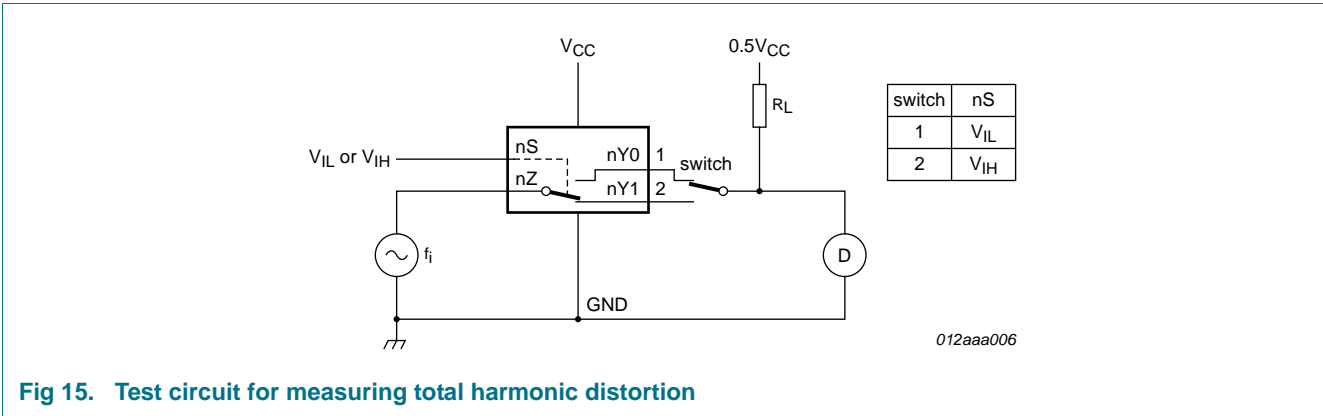


Fig 15. Test circuit for measuring total harmonic distortion

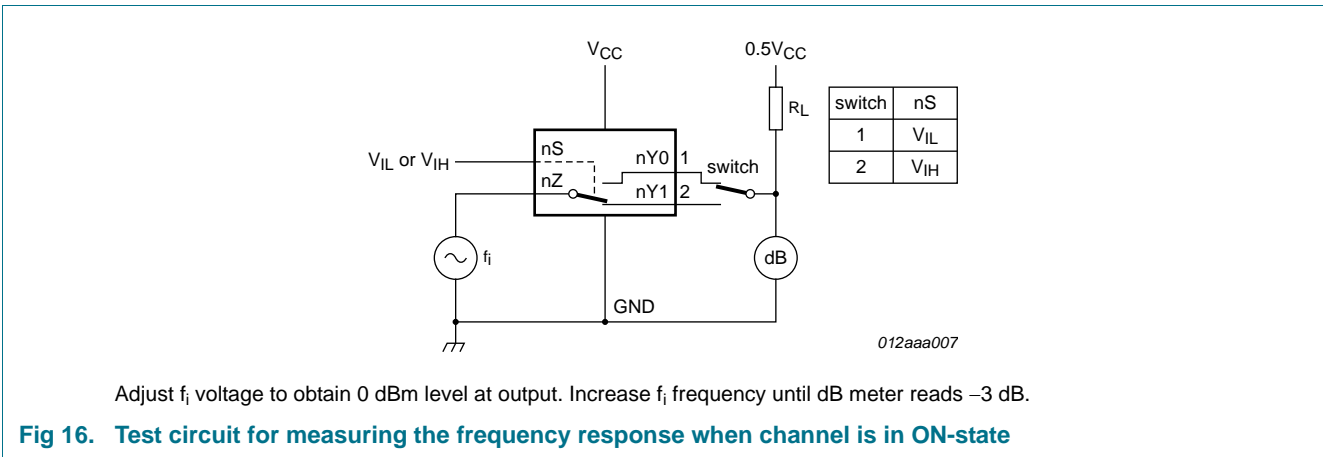


Fig 16. Test circuit for measuring the frequency response when channel is in ON-state

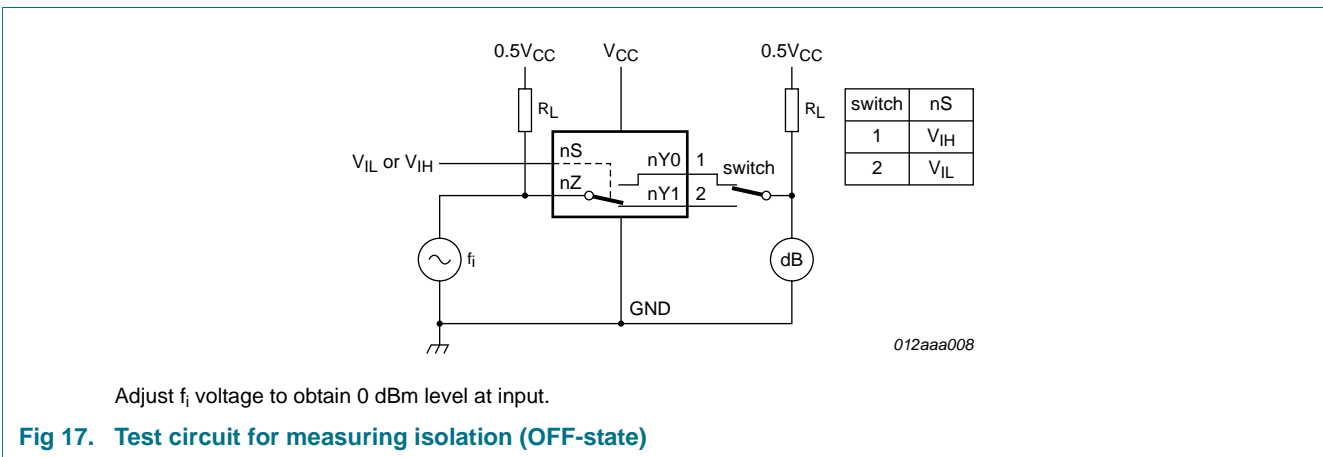
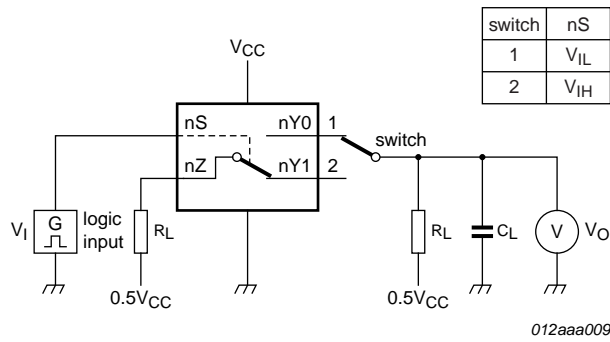
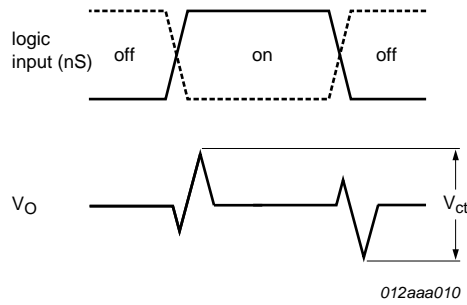


Fig 17. Test circuit for measuring isolation (OFF-state)

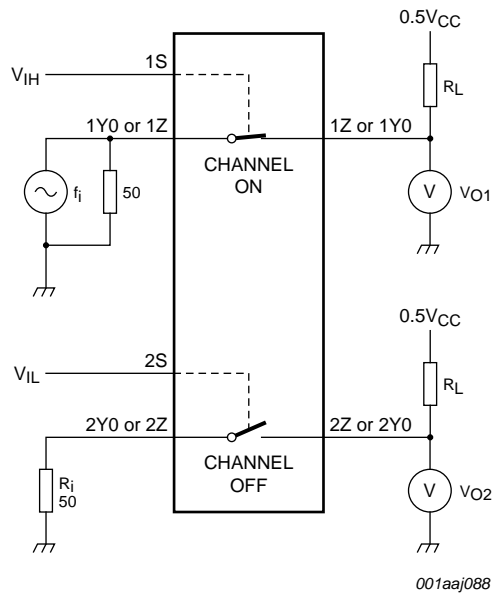


a. Test circuit



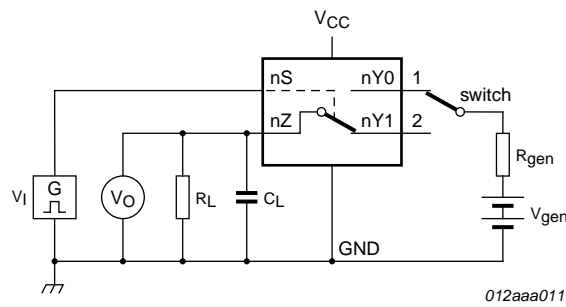
b. Input and output pulse definitions

Fig 18. Test circuit for measuring crosstalk voltage between digital inputs and switch

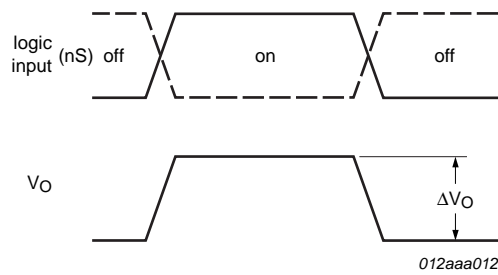


$$20 \log_{10} (V_{O2} / V_{O1}) \text{ or } 20 \log_{10} (V_{O1} / V_{O2}).$$

Fig 19. Test circuit for measuring crosstalk between switches



a. Test circuit.



b. Input and output pulse definitions

Definition: $Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 20. Test circuit for measuring charge injection

13. Package outline

XQFN10: plastic, extremely thin quad flat package; no leads; 10 terminals; body 1.40 x 1.80 x 0.50 mm

SOT1160-1

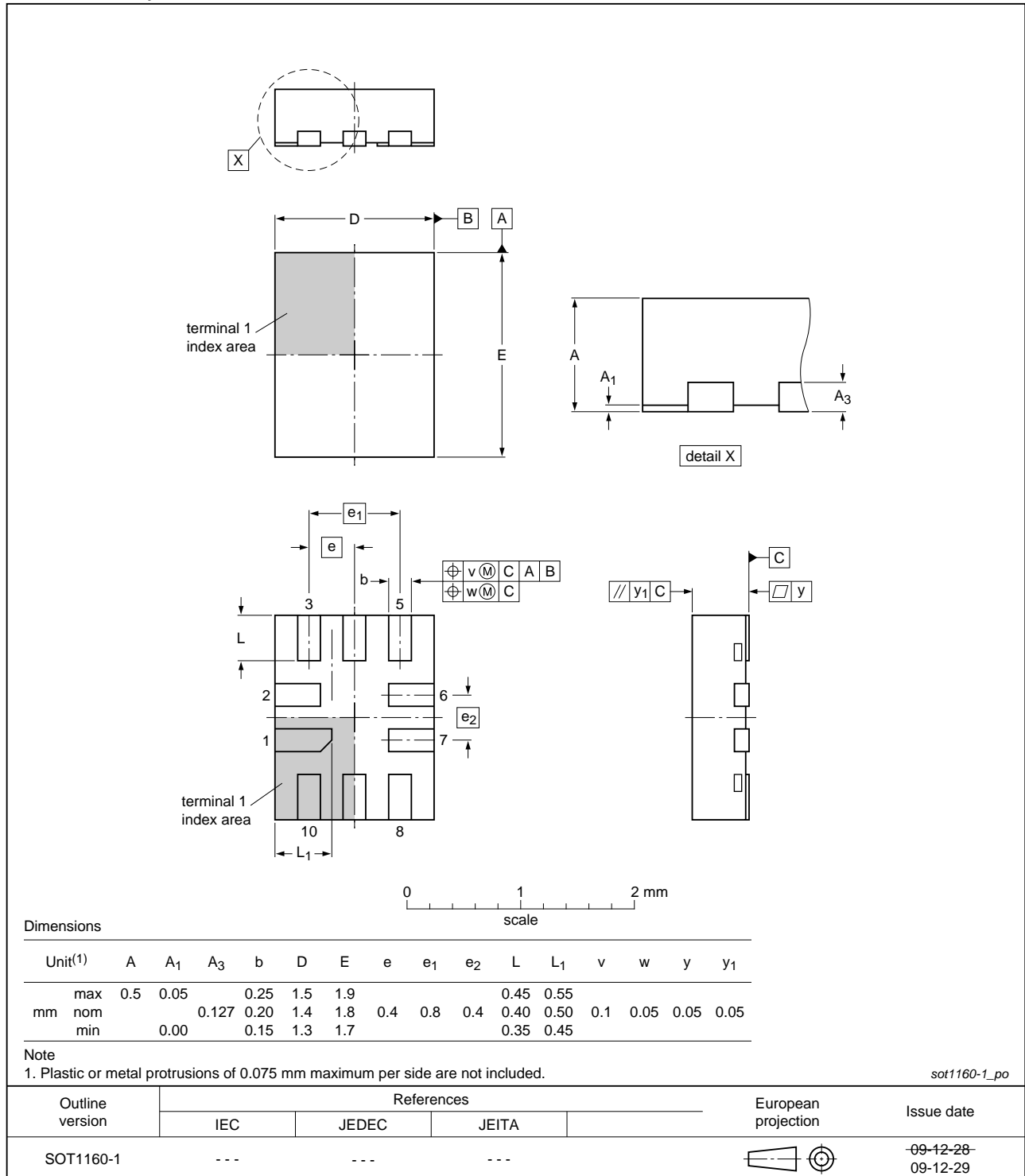


Fig 21. Package outline SOT1160-1 (XQFN10)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3L2267S v.1	20110823	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 23 August 2011

Document identifier: NX3L2267S